

Features

- Plastic package has Underwriters Laboratory Flammability Classification 94V-0
- Glass passivated chip junction
- High surge forward current capability
- Ideal for automated placement
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- Component in accordance to RoHS 2015/863/EU

Mechanical data

- Case: JBF molded plastic body
- Terminals: Plated leads solderable per MIL-STD-750, method 2026
- Polarity: As marked
- Mounting Position: Any

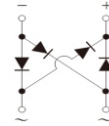
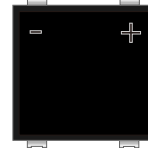
APPLICATIONS

- Used in high frequency AC/DC bridge full wave rectification for SMPS, lighting ballast, adapter, battery charger, home appliances, office equipment, and telecommunication applications.

JBF



HALOGEN
FREE



Maximum Ratings And Electrical Characteristics

(Ratings at 25°C ambient temperature unless otherwise specified, Single phase, half wave, resistive or inductive load. For capacitive load, derate by 20%.)

Parameters	Symbol	RJBF301	RJBF302	RJBF304	RJBF306	RJBF308	RJBF310	Unit
Maximum repetitive peak reverse voltage	V_{RRM}	100	200	400	600	800	1000	V
Maximum average forward rectified current	$I_{F(AV)}$	3.0						A
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC method, Total device)	I_{FSM}	120						A
Rating for fusing (t=8.3ms)	I^2t	59.7						A ² S
Operating junction temperature range	T_j	-55 to 150						°C
Storage temperature range	T_{stg}	-55 to 150						°C

RATINGS AND CHARACTERISTICS OF RJBF301 THRU RJBF310

Electrical Characteristics (Per diode, $T_A=25^{\circ}\text{C}$ Unless otherwise noted)

Parameter	Test Conditions		Symbol	RJBF301	RJBF302	RJBF304	RJBF306	RJBF308	RJBF310	Unit
Instanteous forward voltage	If=3.0A		V _F ¹⁾	1.25						V
Reverse recovery time	If=0.5A,Ir=1A,Irr=0.25A		trr	150			250	500		ns
Reverse current	V _R =V _{RRM}	T _A =25°C	I _R ²⁾	5						μA
		T _A =100°C		70						
		T _A =125°C		250						

Notes: 1.Pulse test: 300 μs pulse width, 1% duty cycle

2.Pulse test: pulse width $\leq 40\text{ms}$

Thermal Characteristics

Parameter	Symbol	JBF	Unit
Typical thermal resistance ³⁾	$R_{\theta JC}$	5.0	$^{\circ}\text{C}/\text{W}$

3.Thermal resistance from per diode junction to case

Fig.1-Forward Current Derating Curve

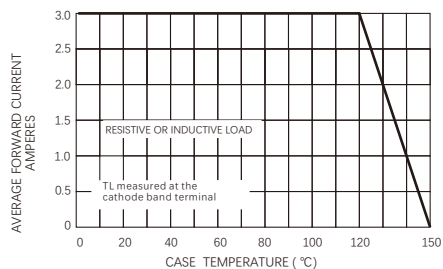


Fig.2-Maximum Non-repetitive Peak Forward Surge Current

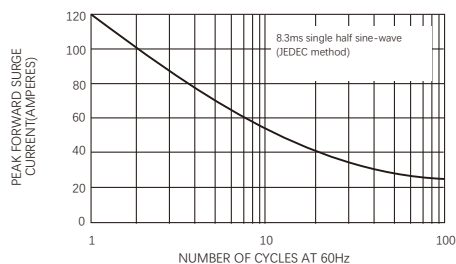


Fig.3-Typical Instantaneous Forward Characteristics

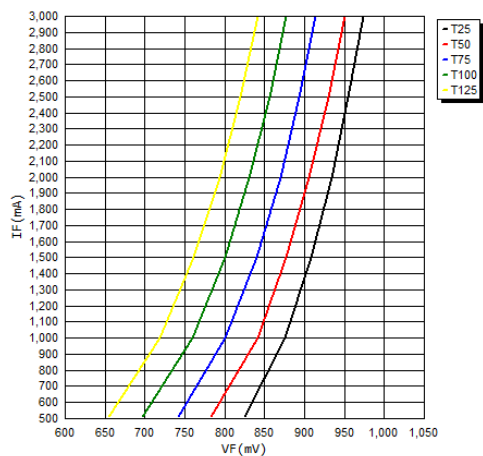
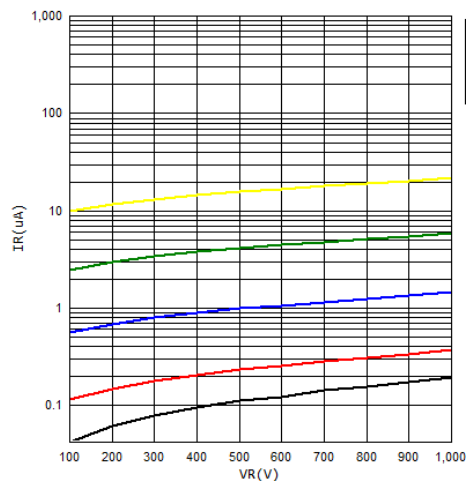
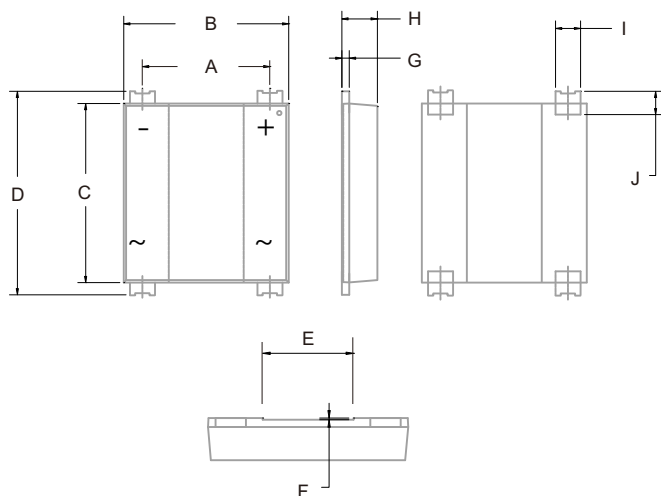


Fig.4-Typical Reverse Characteristics

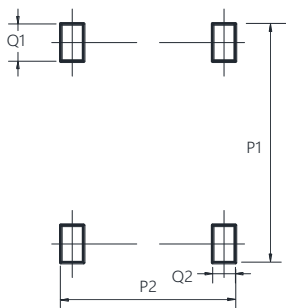


JBF



UNIT:mm		
DIM	MIN	MAX
A	4.80	5.30
B	6.20	7.00
C	7.10	8.20
D	7.90	8.90
E	2.90	3.10
F	0.04	0.08
G	0.15	0.40
H	1.30	1.50
I	0.80	1.20
J	0.70	1.60

Suggested Pad layout



Dimensions in millimeters

Dim	Min
P1	9.15
P2	7.10
Q1	1.80
Q2	2.00

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